

RELIABILITY REPORT FOR

DS31412, Rev A1

Dallas Semiconductor

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Prepared by:

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Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Dallas Semiconductor products and processes:

In addition, Dallas Semiconductor's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

```
AfT = exp((Ea/k)*(1/Tu - 1/Ts)) = tu/ts
AfT = Acceleration factor due to Temperature
tu = Time at use temperature (e.g. 55°C)
ts = Time at stress temperature (e.g. 125°C)
k = Boltzmann's Constant (8.617 x 10-5 eV/°K)
Tu = Temperature at Use (°K)
Ts = Temperature at Stress (°K)
Ea = Activation Energy (e.g. 0.7 ev)
```

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

```
AfV = exp(B*(Vs - Vu))

AfV = Acceleration factor due to Voltage

Vs = Stress Voltage (e.g. 7.0 volts)

Vu = Maximum Operating Voltage (e.g. 5.5 volts)

B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)
```

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

```
Fr = X/(ts * AfV * AfT * N * 2)
X = Chi-Sq statistical upper limit
N = Life test sample size
```

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE: MTTF (YRS): 5405 FITS: 21.1

The parameters used to calculate this failure rate are as follows:

Cf: 60% Ea: 0.7 B: 0 Tu: 25 °C Vu: 5.5 Volts

The reliability data follows. A the start of this data is the device information. This is a description of the device either used as a reliability test vehicle for a process / assembly qualification / monitor or a device used as part of a product qualification / monitor. Following this is the assembly information. This section includes a description of the assembly vehicle used to generate this reliability data for both qualifications and monitors. The next section is the detailed reliability data for each stress found in the qualification / monitor. If there are additional processes or assemblies used as part of this report, a description of each will follow which includes the respective reliability data for that process/ assembly. The reliability data section includes the latest data available.

Device Information:

Device: DS31412

Process: 1P, 4M,0.35um, Sil.P1, Ti/TiN M1-M4 ,BPSG,Masked N+ES

Passivation: Passivation w/Nov TEOS Oxide-Nitride

Die Size: 444 x 438 Number of Transistors: 3100000

Interconnect: Aluminum / 1% Silicon / 0.5% Copper

Gate Oxide Thickness: 75 Å

Assembly Information:

Qualification Vehicle: DS31412
Assembly Site: ASAT
Pin Count: 349
Package Type: CSBGA
Body Size: 27x27x1.5

Mold Compound: Nitto HC-100-XJAA-M

Lead Frame: PCB; BT
Lead Finsh: SnPbAg
Die Attach: CRM1525D
Bond Wire / Size: Au / 1.0 mil
Flammability: UL 94-V0
Moisture Sensitivity Level 3

(JEDEC J-STD20A)

Date Code Range: 0319 to 0319

CONSTRUCTION ANALYSIS

DESCRIPTION DATE CODE CONDITION READPOINT QUANTITY FAILS

PACKAGE, ASSEMBLY P 0319 TO BE SUBMITTED BY ASSEMBLY SITE 5 WKS 0 0

Total: 0

ELECTRICAL CHARACTERIZATION

DESCRIPTION DATE CODE CONDITION READPOINT QUANTITY FAILS

TEMP CYCLE	0319	-55C TO 125C	1000	CYS Tota		0 0
DESCRIPTION	DATE CODE	CONDITION	REA	POINT	QUANTITY	FAILS
TEMPERATURE CYCL	.E					
OTOTAGE LIFE	0019	1000	1000	Tot		0
STORAGE LIFE	0319	150C	1000	HRS	76	0
DESCRIPTION	DATE CODE	CONDITION	REAL	POINT	QUANTITY	FAILS
STORAGE LIFE						
			ŭ	Tota		0
CONVECTION REFLOW		220C	3	PASS	244	0
STORAGE LIFE MOISTURE SOAK	0319	125C 30C/60% R.H.	48 192	HRS HRS	244 244	
PRECONDITIONING L DESCRIPTION		CONDITION	REAI	OPOINT	QUANTITY	FAILS
PDECONDITION ::	EVEL 0			100	aı.	- 0
MARK PERMANENCY		JESD22-B107	6	DYS Tot	6	0
BALL SHEAR		JESD22-B117	6	DYS	6	0
PHYSICAL DIMENSIONS		JESD22-B100	6	DYS	6	0
X-RAY	0319	MIL-STD-883-2012 : TOP & SIDE VIEW	6	DYS	6	0
DESCRIPTION	DATE CODE	CONDITION	REAI	POINT	QUANTITY	FAILS
PACKAGE TESTS						
				Tota	_	0
HIGH TEMP OP LIFE	0319	125C, 3.5 VOLTS		HRS	46	0
OPERATING LIFE DESCRIPTION	DATE CODE	CONDITION	REAI	OPOINT	QUANTITY	FAILS
				Tota	al:	0
PRECONDITION U/S		J-STD-020	3	DYS	8	0
EXTERNAL VISUAL		J-STD-020, 6.1a	3	DYS	8	0
CONVECTION REFLOW		220C	3	PASS	8	0
MOISTURE SOAK		30C/60% R.H.	192	HRS	8	
STORAGE LIFE		125C	48	HRS	8	J
ULTRASOUND	0010	J-STD-020, 6.1a J-STD-020	3	DYS	8	0
EXTERNAL VISUAL	0319		3	DYS	8	0
MOISTURE SENSITIVI DESCRIPTION	_	CONDITION	REAI	OPOINT	QUANTITY	FAILS
MOIOTURE OF MOITH	T)/ E)/E 0			Tota	aı:	3
LATCH-UP	0319	JESD78, Vsupply TEST 125C	2	DYS	6	0
LATCH-UP	0319	JESD78, I-TEST 125C	2	DYS	6	0
ESD SENSITIVITY	0319	EOS/ESD S5.1 HBM 4000 VOLTS	1	PUL'S	3	3
ESD SENSITIVITY	0319	EOS/ESD S5.1 HBM 2000 VOLTS	1	PUL'S	3	0
ESD SENSITIVITY	0319	EOS/ESD S5.1 HBM 1000 VOLTS	1	PUL'S	3	C

TEMPERATURE HUMIDITY BIAS

DESCRIPTION DATE CODE CONDITION READPOINT QUANTITY FAILS

BIASED MOISTURE 0319 85/85, 3.5 VOLTS 1000 HRS 43 0

Total: 0

FAILURE RATE: MTTF (YRS): 5405 FITS: 21.1